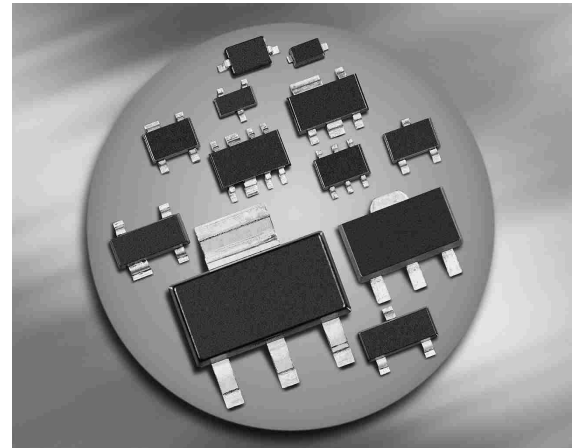


**PNP Silicon Switching Transistors**

- High DC current gain: 0.1 mA to 100 mA
- Low collector-emitter saturation voltage
- For SMBT3906S and SMBT3906U:  
Two (galvanic) internal isolated transistor with good matching in one package
- Complementary types:  
SMBT3904...MMBT3904 (NPN)
- SMBT3906S/ U: for orientation in reel  
see package information below
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
SMBT3906/ MMBT3906	s2A	1=B	2=E	3=C	-	-	-	SOT23
SMBT3906S	s2A	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
SMBT3906U	s2A	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	40	V
Collector-base voltage	$V_{CBO}$	40	
Emitter-base voltage	$V_{EBO}$	6	
Collector current	$I_C$	200	mA
Total power dissipation-	$P_{tot}$		mW
$T_S \leq 71^\circ\text{C}$ , SOT23, MMBT3906		330	
$T_S \leq 115^\circ\text{C}$ , SOT363, MMBT3906S		250	
$T_S \leq 107^\circ\text{C}$ , SC74, MMBT3906U		330	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> SMBT3906/ MMBT3906	$R_{thJS}$	$\leq 240$	mW
SMBT3906S		$\leq 140$	
SMBT3906U		$\leq 130$	

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	40	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	40	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 30 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	50	nA
DC current gain <sup>1)</sup> $I_C = 100 \mu\text{A}, V_{CE} = 1 \text{ V}$ $I_C = 1 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}$	$h_{FE}$	60 80 100 60 30	- - - - -	- - 300 - -	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	$V_{CEsat}$	- -	- -	0.25 0.4	V
Base emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$	$V_{BEsat}$	0.65 -	- -	0.85 0.95	

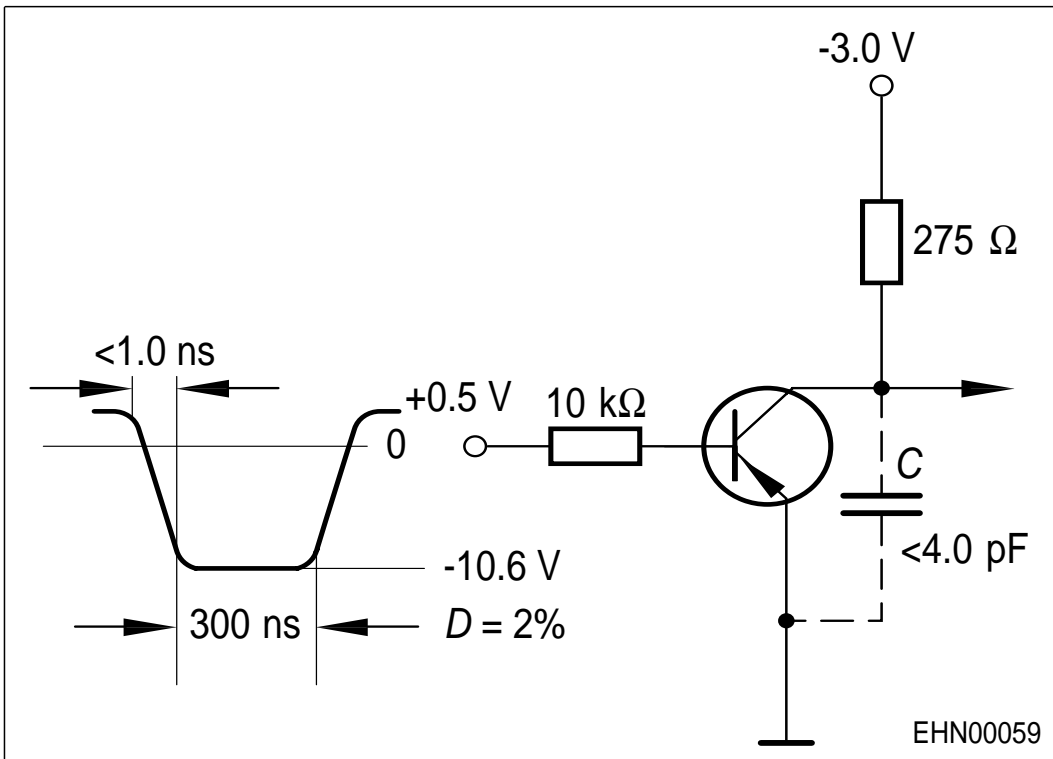
<sup>1)</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

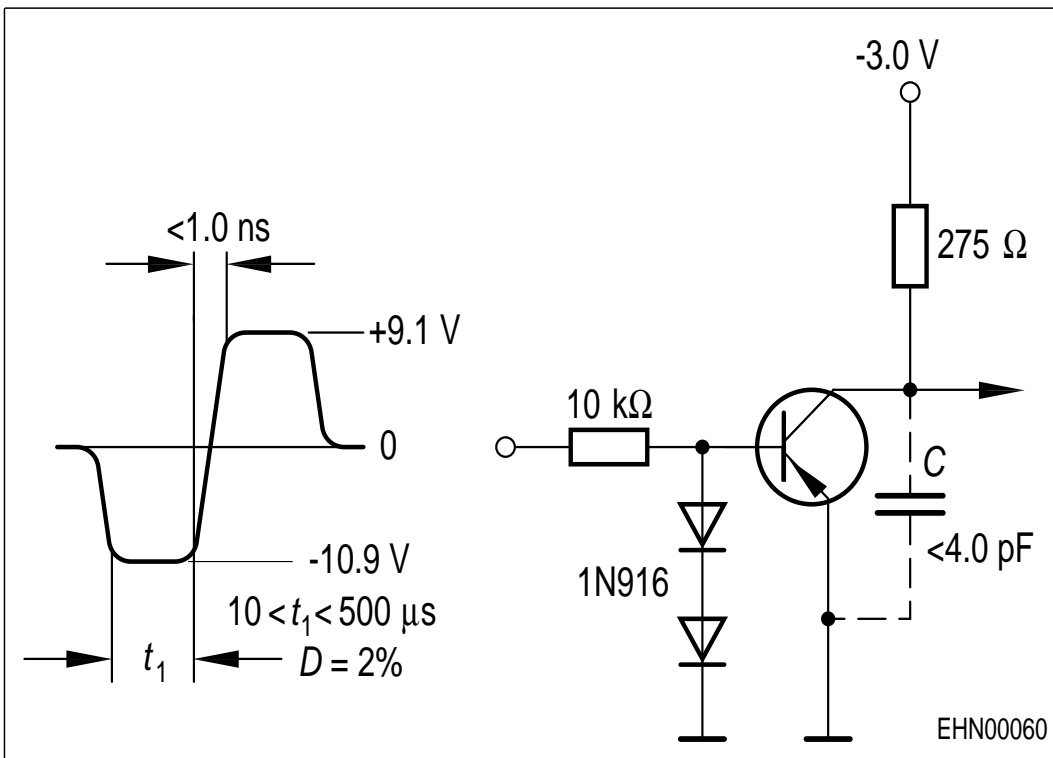
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 10\text{ mA}$ , $V_{CE} = 20\text{ V}$ , $f = 100\text{ MHz}$	$f_T$	250	-	-	MHz
Collector-base capacitance $V_{CB} = 5\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	-	3.5	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	-	10	
Delay time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 1\text{ mA}$ , $V_{BE(off)} = 0.5\text{ V}$	$t_d$	-	-	35	ns
Rise time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 1\text{ mA}$ , $V_{BE(off)} = 0.5\text{ V}$	$t_r$	-	-	35	
Storage time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = I_{B2} = 1\text{ mA}$	$t_{stg}$	-	-	225	
Fall time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = I_{B2} = 1\text{ mA}$	$t_f$	-	-	75	
Noise figure $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $\Delta f = 200\text{ Hz}$ , $R_S = 1\text{ k}\Omega$	$F$	-	-	4	dB

Test circuit

Delay and rise time

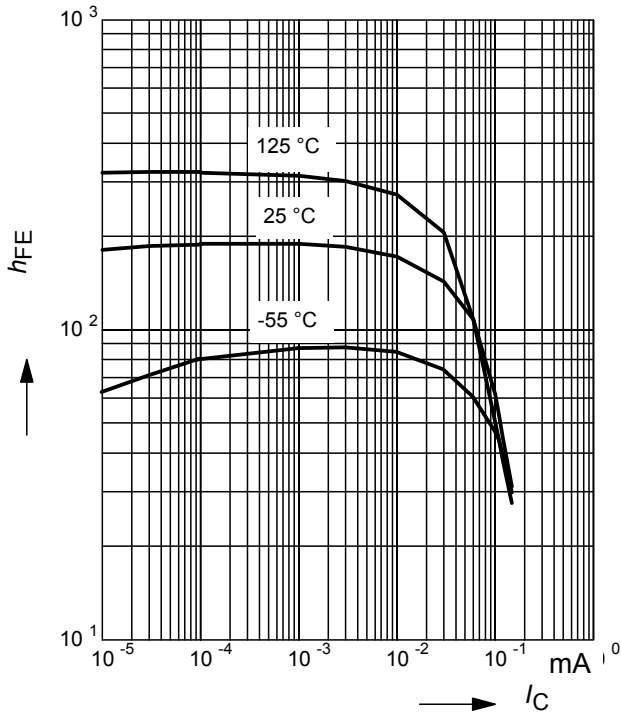


Storage and fall time



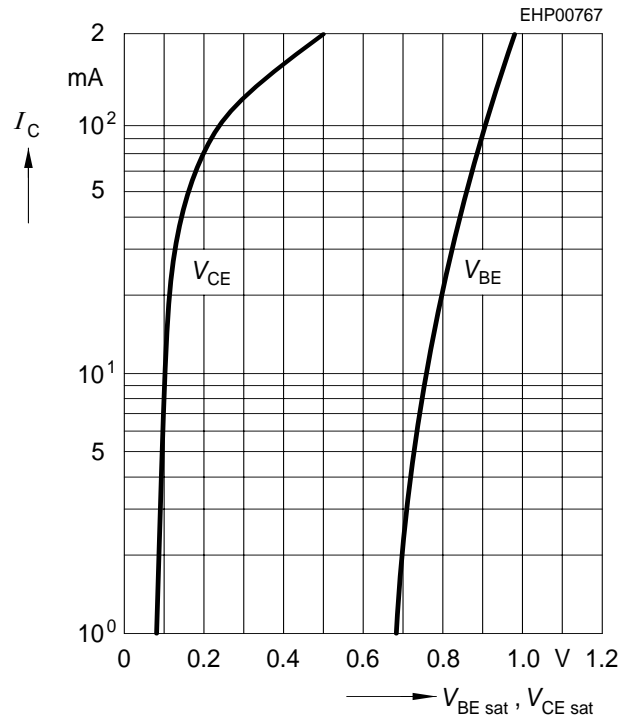
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 1\text{ V}$



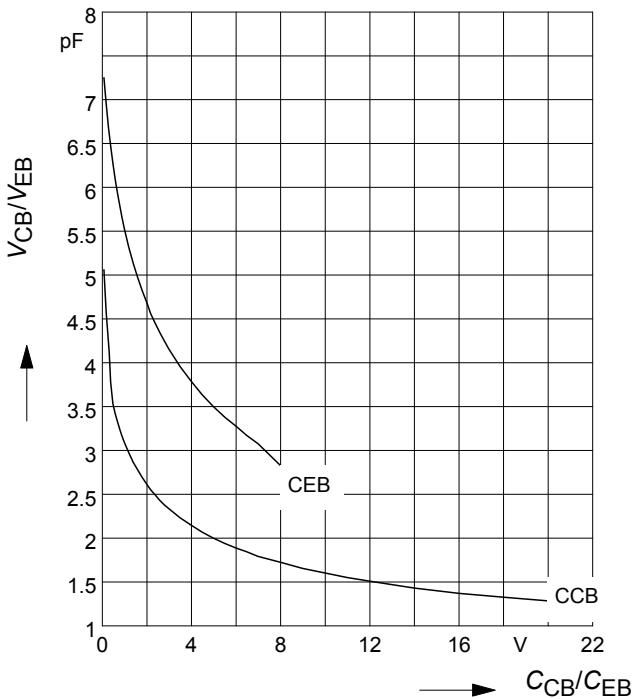
**Saturation voltage  $I_C = f(V_{BEsat}; V_{CEsat})$**

$h_{FE} = 10$



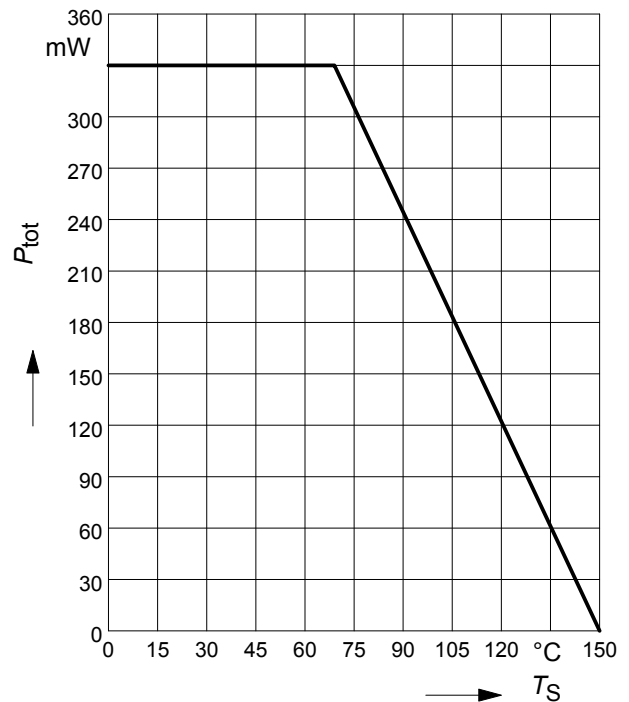
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

**Emitter-base capacitance  $C_{eb} = f(V_{EB})$**



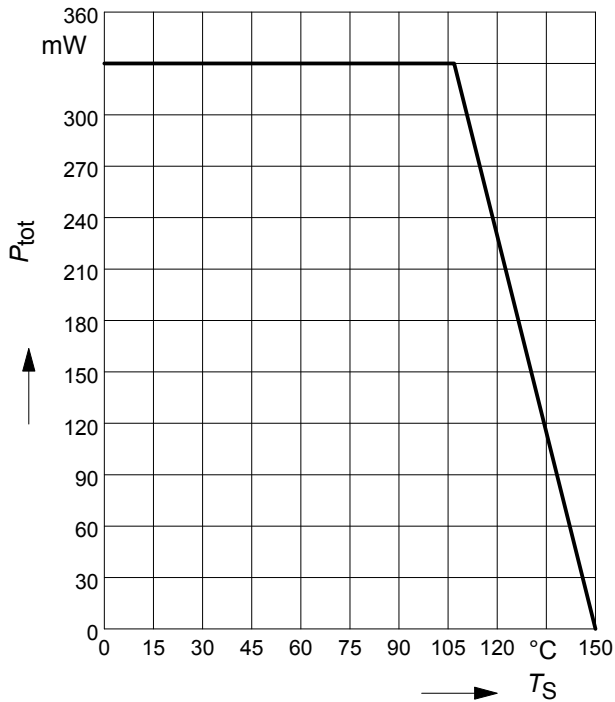
**Total power dissipation  $P_{tot} = f(T_S)$**

SMBT3906



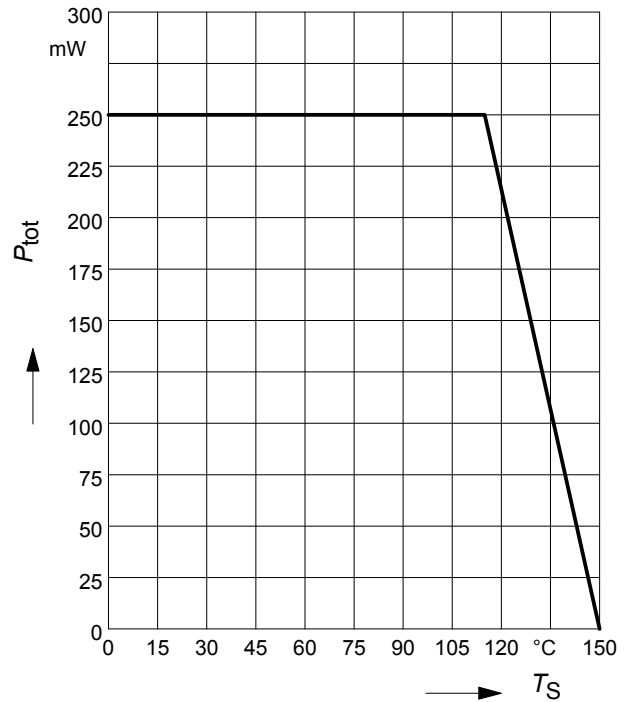
**Total power dissipation  $P_{tot} = f(T_S)$**

SMBT3906U



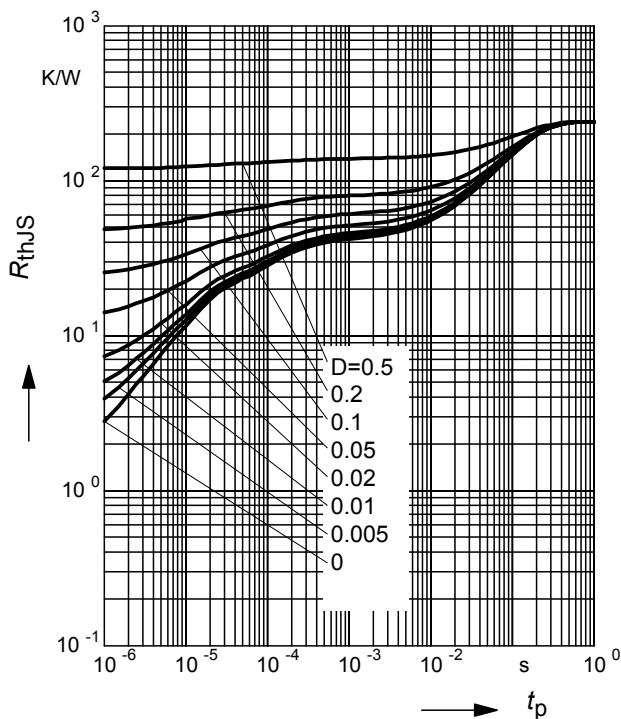
**Total power dissipation  $P_{tot} = f(T_S)$**

SMBT3906S



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

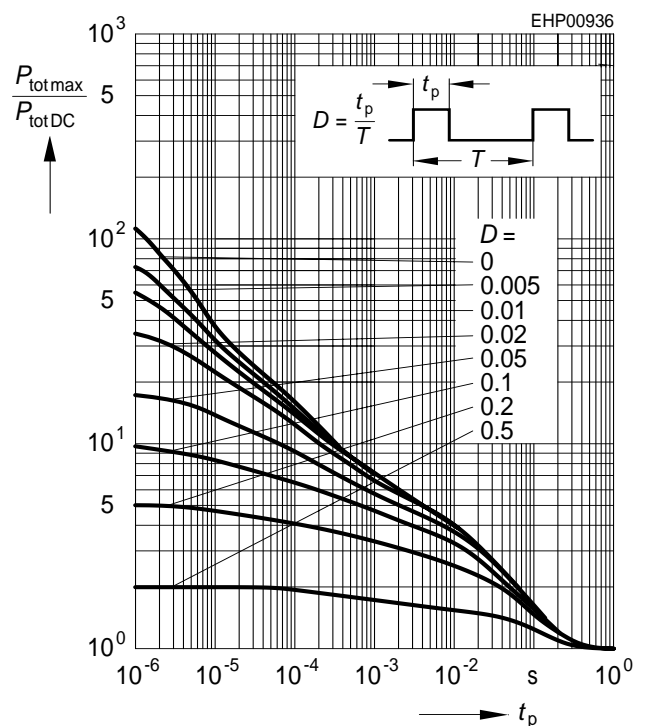
SMBT3906



**Permissible Pulse Load**

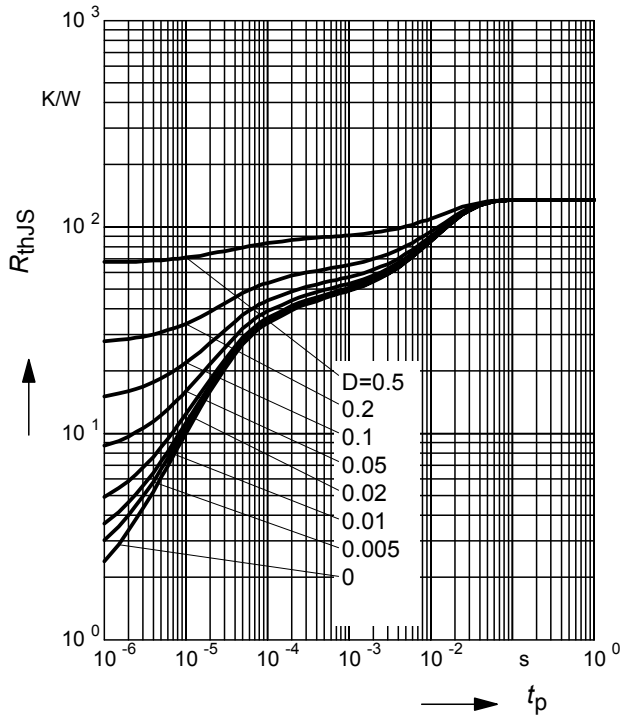
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3906



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

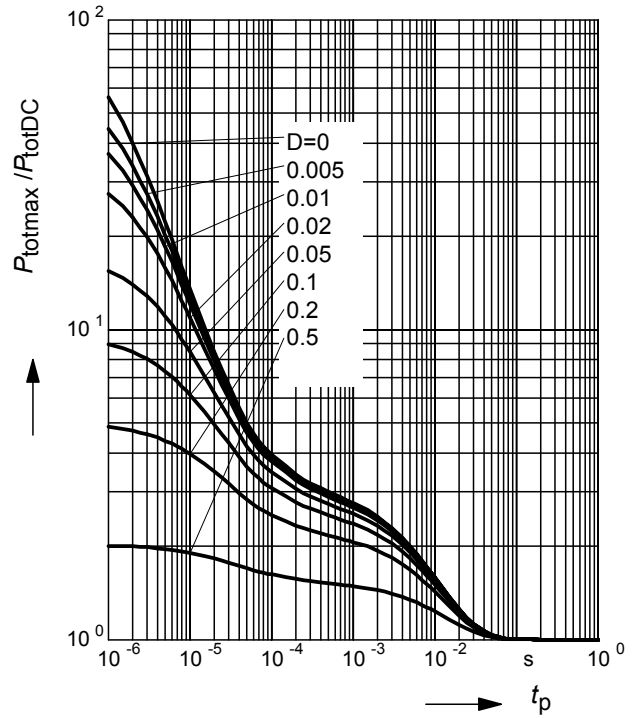
SMBT3906U



**Permissible Pulse Load**

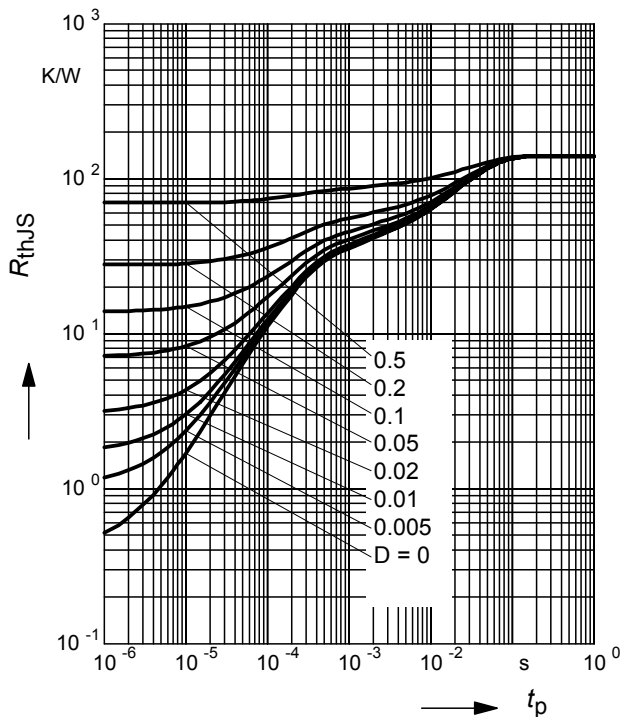
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3906U



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

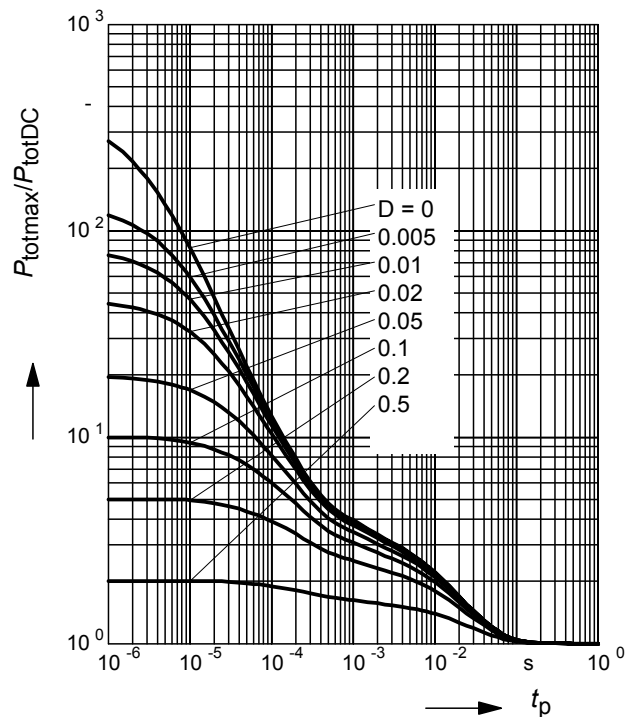
SMBT3906S



**Permissible Pulse Load**

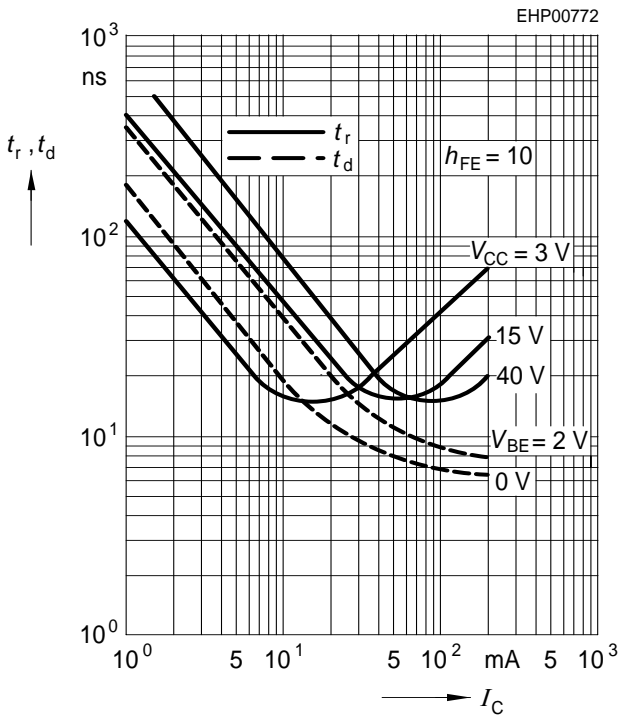
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3906S

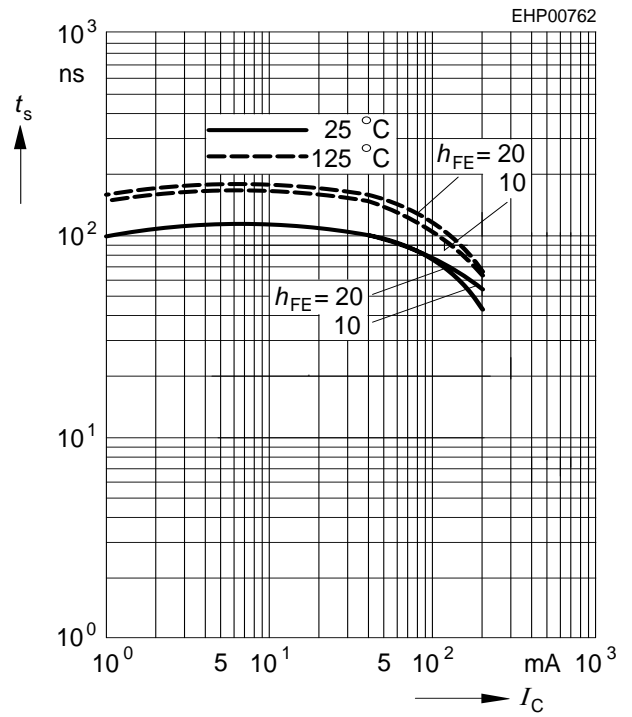


Delay time  $t_d = f(I_C)$

Rise time  $t_r = f(I_C)$

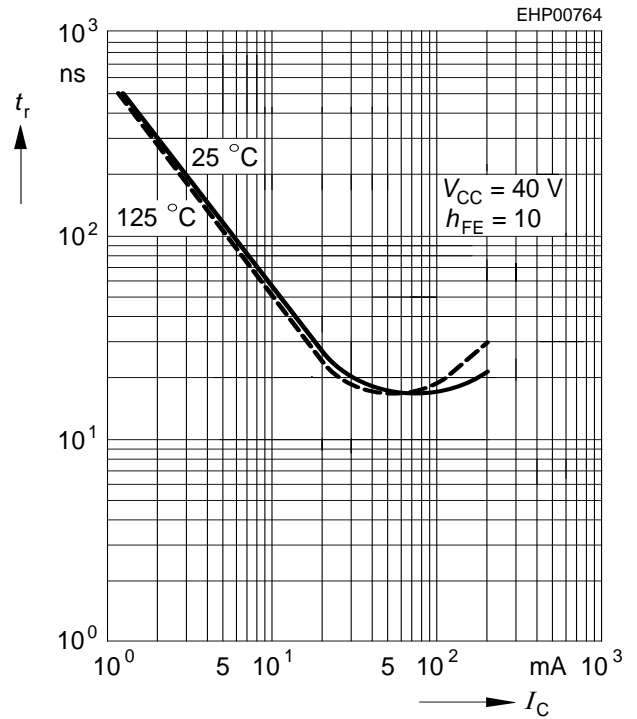
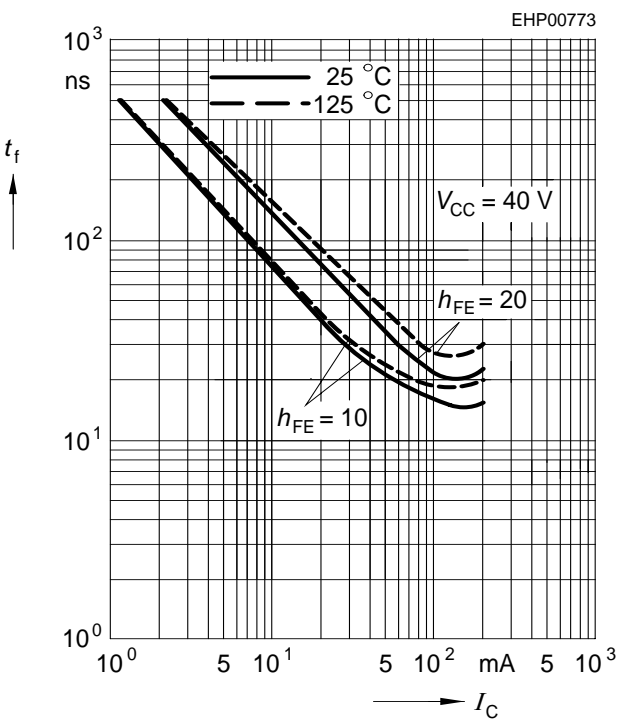


Storage time  $t_{stg} = f(I_C)$



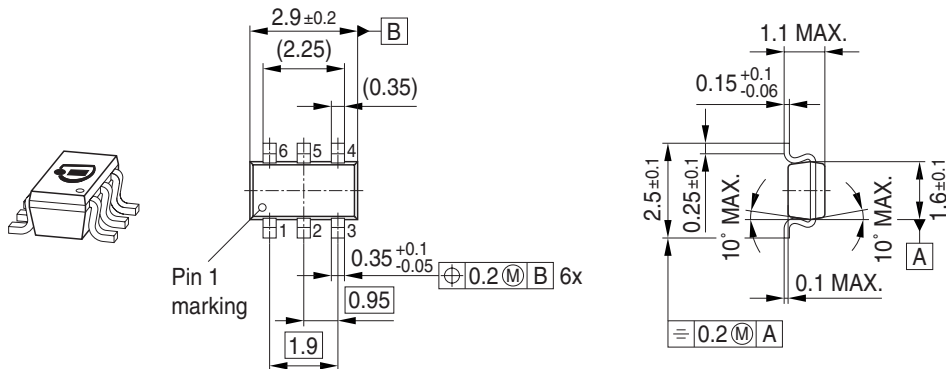
Fall time  $t_f = f(I_C)$

Rise time  $t_r = f(I_C)$

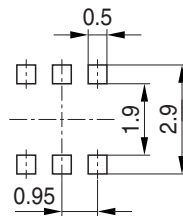




Package Outline

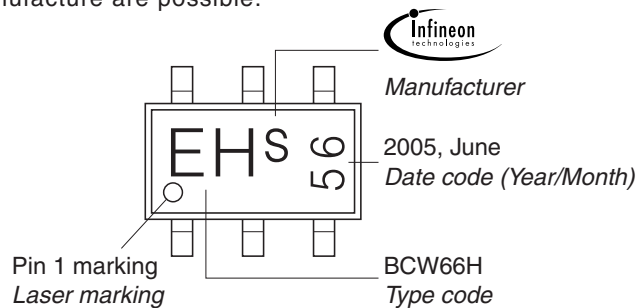


Foot Print



Marking Layout (Example)

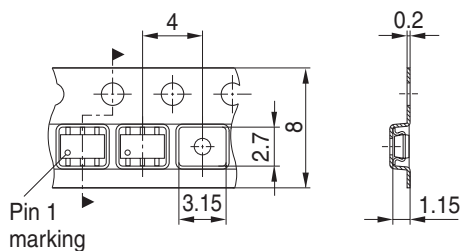
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print

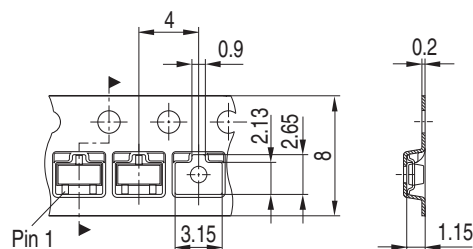


Marking Layout (Example)

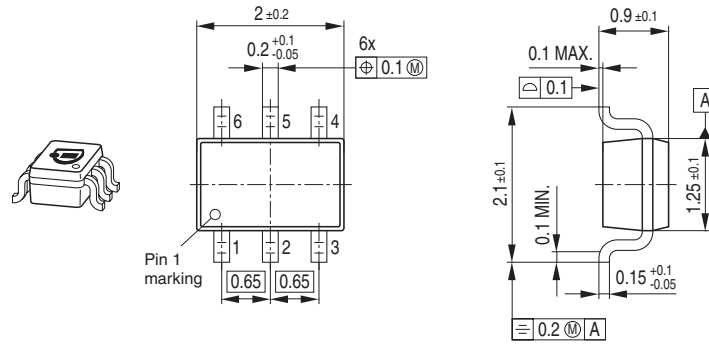


Standard Packing

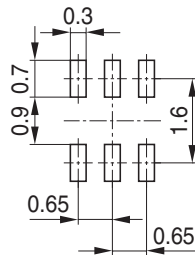
Reel  $\phi$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\phi$ 330 mm = 10.000 Pieces/Reel



### Package Outline

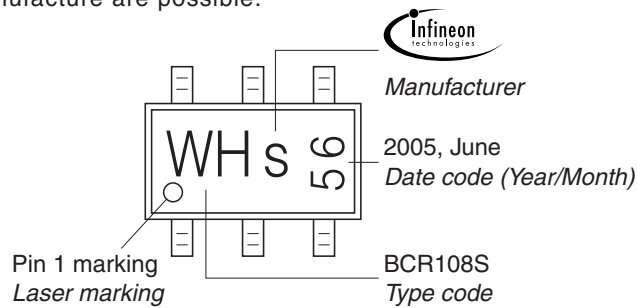


### Foot Print



### Marking Layout (Example)

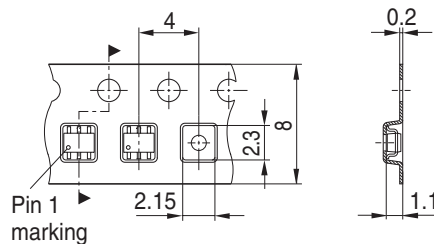
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